

In the Specification:

Please substitute the following Title of the application for the Title as originally filed at all occurrences in the application:

ELECTROSTATIC DISCHARGE SEMICONDUCTOR PROTECTION
CIRCUIT OF REDUCED AREA

Please substitute the following paragraphs for the corresponding paragraphs beginning at the indicated location in the specification as originally filed.

Page 10, line 7+:

Figure 2 is a circuit diagram showing the protection circuit of the semiconductor device according to ~~according~~ the first embodiment of the invention.

Page 13, line 7+:

~~Beside Besides~~, a contact hole 40 is formed above the N-type diffusion region 33 forming the source region. The metal gate wiring 38 is arranged in the contact hole 40. The metal gate wiring 38 is connected to terminal T2 as shown at 41 of Figure 5.

Page 13, line 27+:

Further, a high-density N-type diffused region 45 is formed in on the periphery 50 of the P-type diffused region 44. The N-type diffused region 45 is contacted to the P-type diffused region 44 and forms a PN junction 46 together with the P-type diffused region 44. The PN junction 46 functions as the diode D1. At this time, as the P-type diffused region 44 and the N-type diffused region 45 respectively forming the PN junction 46 become ~~a~~ high-density impurities diffused regions, the quantity of withstand voltage can be enhanced, compared with a parasitic diode formed by the

semiconductor substrate 31 and the well region 32, and the impedance can be reduced, as schematically depicted (in dashed lines) as contact hole 49 and wiring 48.